

Silicon NPN Power Transistor

2SC5130

DESCRIPTION

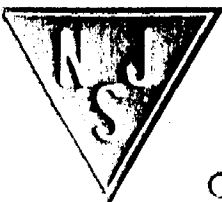
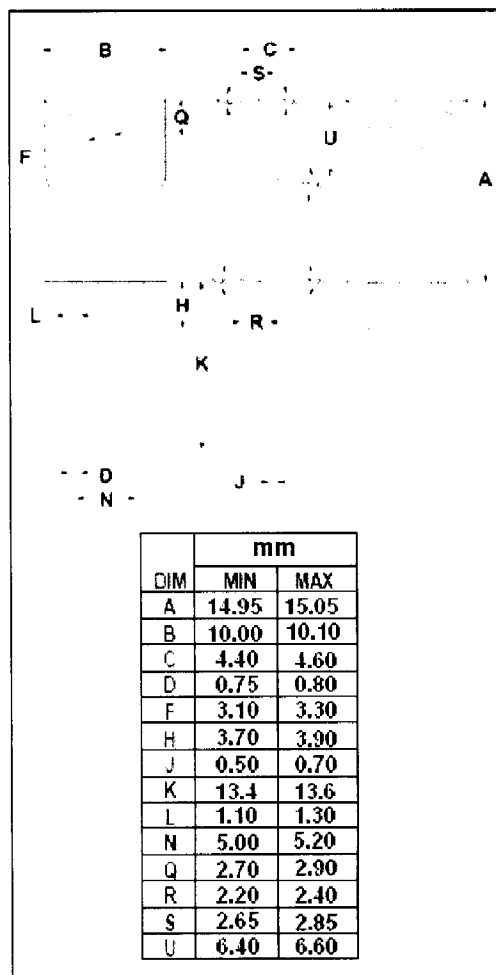
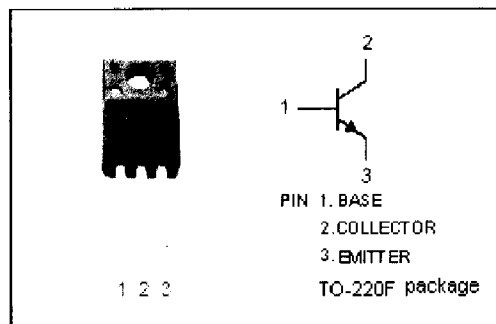
- Collector-Emitter Breakdown Voltage-
 $V_{(BR)CEO} = 400V(\text{Min})$
- High Switching Speed

APPLICATIONS

- Designed for switching regulator and general purpose applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	600	V
V_{CEO}	Collector-Emitter Voltage	400	V
V_{EBO}	Emitter-Base Voltage	10	V
I_C	Collector Current-Continuous	5	A
I_{CM}	Collector Current-Peak	10	A
I_B	Base Current-Continuous	2	A
P_C	Collector Power Dissipation @ $T_c=25^\circ\text{C}$	30	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55~150	$^\circ\text{C}$



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ELECTRICAL CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 25mA; I _B = 0	400			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 1.5A; I _B = 0.3A			0.5	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 1.5A; I _B = 0.3A			1.3	V
I _{CBO}	Collector Cutoff Current	V _{CB} = 500V; I _E = 0			100	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = 10V; I _C = 0			10	μ A
h _{FE}	DC Current Gain	I _C = 1.5A; V _{CE} = 4V	10		30	
C _{OB}	Output Capacitance	I _E = 0; V _{CB} = 10V; f= 1MHz		30		pF
f _T	Current-Gain—Bandwidth Product	I _E = -0.3A; V _{CE} = 12V		20		MHz

Switching Times

t _{on}	Turn-On Time	I _C = 1.5A; I _{B1} = 0.15A; I _{B2} = -0.3A; V _{CC} = 200V; R _L = 133 Ω			1.0	μ s
t _{stg}	Storage Time				2.0	μ s
t _f	Fall Time				0.3	μ s